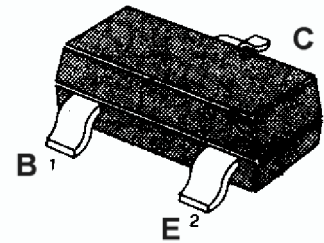


APPLICATION:Low Frequency Amplifier

MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	-50	V
Collector-emitter voltage	V _{CEO}	-40	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-100	mA
Collector Power Dissipation	P _C	150	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C

SOT-23


1.Base 2.Emitter 3. Collector

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	60		1000		V _{CE} = -6V, I _C = -1mA
Collector Cut-off Current	I _{CBO}			-0.1	μA	V _{CB} = -40V, I _E =0
Emitter Cut-off Current	I _{EBO}			-0.1	μA	V _{EB} = -5V, I _C =0
Collector-Base Breakdown Voltage	BV _{CBO}	-50			V	I _C = -0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-40			V	I _C = -1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E = -0.1mA, I _C =0
Base-Emitter Voltage	V _{BE}			-0.8	V	V _{CE} = -6V, I _C = -1mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-0.5	V	I _C = -30mA, I _B = -3mA
Gain bandwidth product	f _T	150			MHz	I _C = -10mA, V _{CE} = -6V

h_{FE} Classification And Marking

Print Mark	M3	M4	M5	M6	M7	M8
Classification	M3	M4	M5	M6	M7	M8
h _{FE}	60~90	90~135	135~200	200~400	400~600	600~1000